

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

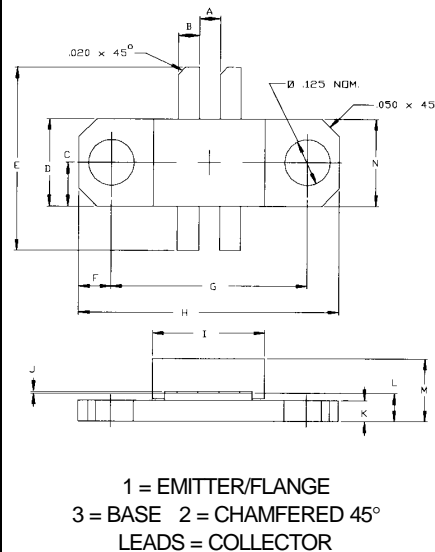
The **TPV5051-1** is Designed for AB Push Pull, Common Emitter from 470 to 860 MHz Applications.

MAXIMUM RATINGS

I_C	2.6 A (EACH SIDE)
V_{CE}	25 V
P_{DISS}	65 W @ $T_C = 25^\circ\text{C}$ (TOTAL)
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
q_{JC}	2.5°C/W

PACKAGE STYLE BMA 2A

	MIN: (In/mm)	MAX: (In/mm)
A	.060/1.52	.060/1.52
B	.055/1.40	.065/1.65
C	.124/3.15	.124/3.15
D	.234/6.17	.253/6.34
E	.635/16.13	.665/16.89
F	.092/.234	.092/.234
G	.555/14.10	.565/14.35
H	.739/18.77	.749/19.02
I	.315/8.00	.327/8.31
J	.002/0.05	.006/0.15
K	.055/1.40	.065/1.65
L	.075/1.91	.095/2.41
M		.190/4.83
N	.245/6.22	.257/6.53



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 40\text{ mA}$	25			V
BV_{CBO}	$I_C = 20\text{ mA}$	45			V
BV_{EBO}	$I_E = 6.0\text{ mA}$	4.0			V
h_{FE}	$V_{CE} = 20\text{ V}$ $I_C = 800\text{ mA}$	10			---
C_{ob}	$V_{CB} = 28\text{ V}$ $f = 1.0\text{ MHz}$ (EACH SIDE)			40	pF
P_G	$V_{CE} = 28\text{ V}$ $P_{out} = 50\text{ W}$ $I_q = 2 \times 100\text{ mA}$	6.5			dB
h_c	$f = 860\text{ MHz}$	45			%